

Silicon NPN Power Transistors

2SC4531

DESCRIPTION

- With TO-3P(H)IS package
- High voltage,high speed
- Low saturation voltage
- Bult-in damper diode

APPLICATIONS

- Horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

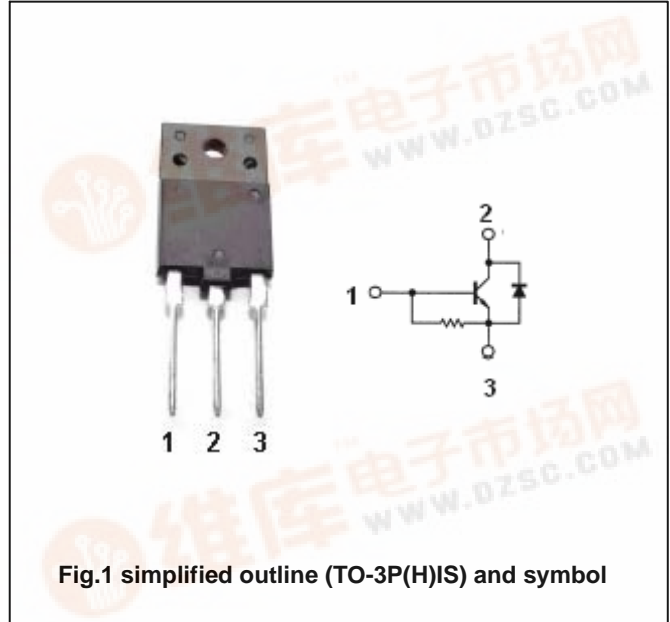


Fig.1 simplified outline (TO-3P(H)IS) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		10	A
I _{CM}	Collector current-Peak		20	A
I _B	Base current		5	A
P _C	Total power dissipation	T _C =25	50	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =200mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =7A; I _B =1.7A			5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =7A; I _B =1.7A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0	66	100	200	mA
h _{FE}	DC current gain	I _C =1A; V _{CE} =5V	8			
C _{ob}	Collector output capacitance	I _E =0; V _{CB} =10V, f=1MHz		210		pF
V _F	Diode forward voltage	I _F =7A		1.5	1.8	V
f _T	Transition frequency	I _C =0.1A; V _{CE} =10V	1	3		MHz

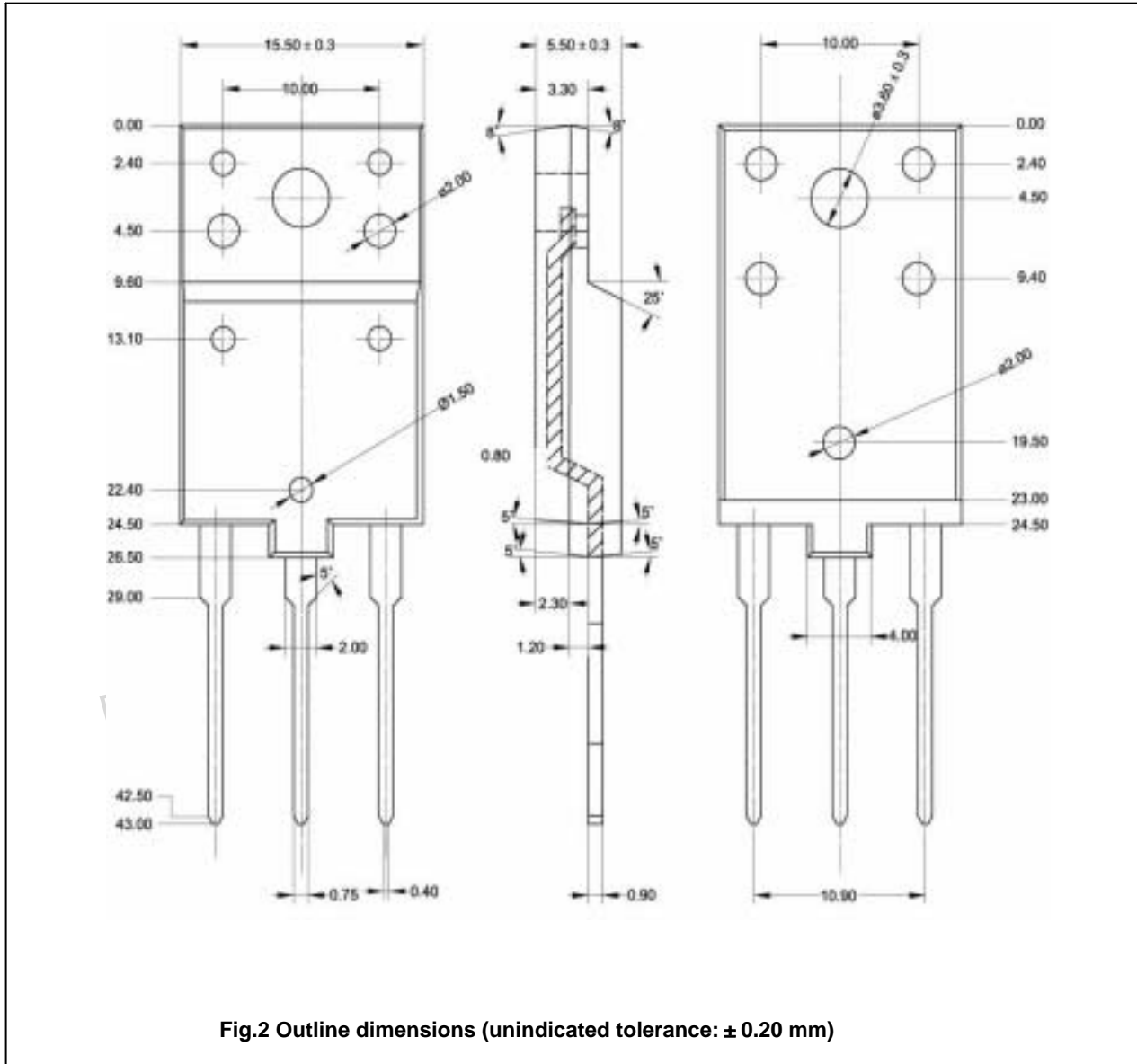
Switching times resistive load

t _s	Storage time	I _{CP} =7A; I _{B1} =1.4A I _{B2} =-2.8A; R _L =28.5		1.8	2.5	μs
t _f	Fall time			0.1	0.2	μs

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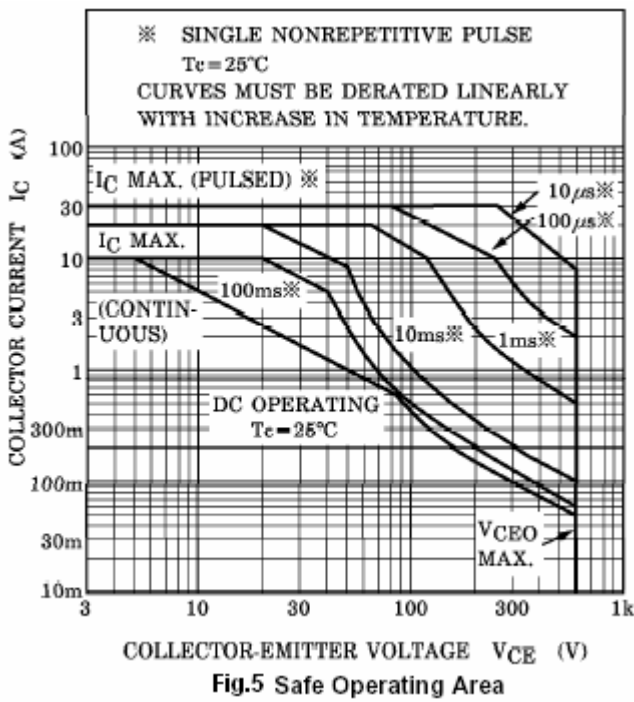
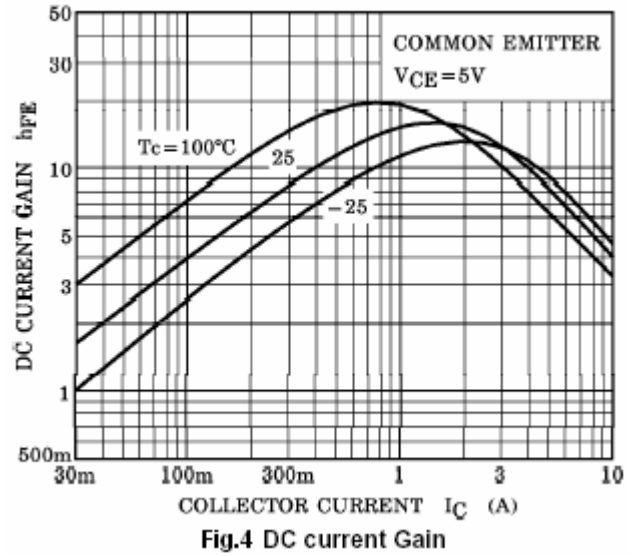
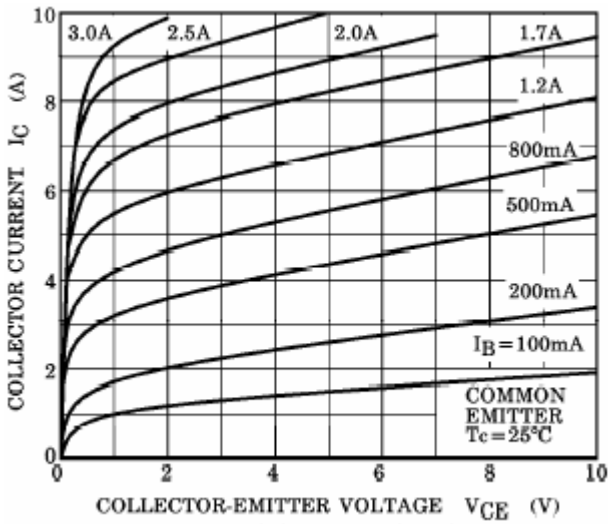
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PACKAGE OUTLINE



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EMICONDUTOR